

# Maciej Bugajski

## List of Publications by Citations

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128  
papers

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18  
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g-index

153  
ext. papers

1,292  
ext. citations

2.2  
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3.73  
L-index

#	Paper	IF	Citations
128	Concentration-dependent absorption and photoluminescence of n-type InP. <i>Journal of Applied Physics</i> , <b>1985</b> , 57, 521-530	2.5	174
127	Energy bands of ternary alloy semiconductors: Coherent-potential-approximation calculations. <i>Physical Review B</i> , <b>1983</b> , 28, 7105-7114	3.3	48
126	Native acceptor levels in Ga-rich GaAs. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 596-599	2.5	45
125	Acceptor-bound magnetic polarons in Cd <sub>1-x</sub> MnxTe. <i>Physical Review B</i> , <b>1988</b> , 38, 10512-10516	3.3	43
124	Complementary thermoreflectance and micro-Raman analysis of facet temperatures of diode lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 071104	3.4	35
123	Monolithic high-index contrast grating: a material independent high-reflectance VCSEL mirror. <i>Optics Express</i> , <b>2015</b> , 23, 11674-86	3.3	33
122	Investigation of thermal properties of mid-infrared AlGaAs/GaAs quantum cascade lasers. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 043112	2.5	30
121	Mid-IR quantum cascade lasers: Device technology and non-equilibrium Green's function modeling of electro-optical characteristics. <i>Physica Status Solidi (B): Basic Research</i> , <b>2014</b> , 251, 1144-1157	1.3	25
120	Nonthermal carrier distributions in the subbands of 2-phonon resonance mid-infrared quantum cascade laser. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 061110	3.4	25
119	Analysis of Free-Space Optics Development. <i>Metrology and Measurement Systems</i> , <b>2017</b> , 24, 653-674		24
118	Advances in self-assembled semiconductor quantum dot lasers. <i>Microelectronics Journal</i> , <b>2005</b> , 36, 950-958		24
117	Diamagnetic shift of exciton energy levels in GaAs-Ga <sub>1-x</sub> Al <sub>x</sub> As quantum wells. <i>Solid State Communications</i> , <b>1986</b> , 60, 669-673	1.6	24
116	Thermoreflectance study of facet heating in semiconductor lasers. <i>Materials Science in Semiconductor Processing</i> , <b>2006</b> , 9, 188-197	4.3	23
115	Analysis of thermal images from diode lasers: Temperature profiling and reliability screening. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 203503	3.4	23
114	MBE growth of strain-compensated InGaAs/InAlAs/InP quantum cascade lasers. <i>Journal of Crystal Growth</i> , <b>2017</b> , 466, 22-29	1.6	19
113	Spatially resolved thermoreflectance study of facet temperature in quantum cascade lasers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 1227-1232	1.6	19
112	Determination of the nitrogen doping of liquid phase epitaxy GaP and Ga <sub>x</sub> In <sub>1-x</sub> P alloys by optical absorption and photoluminescence. <i>Journal of Applied Physics</i> , <b>1983</b> , 54, 5358-5362	2.5	19

111	Optical characterization of semi-insulating GaAs: Determination of the Fermi energy, the concentration of the midgap EL2 level and its occupancy. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 511-513	3.4	18
110	Molecular-beam epitaxy growth and characterization of mid-infrared quantum cascade laser structures. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 565-569	1.8	17
109	The influence of the growth temperature and interruption time on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 2785-2792	1.6	17
108	Comprehensive self-consistent three-dimensional simulation of an operation of the GaAs-based oxide-confined 1.3- $\mu$ m quantum-dot (InGa)As/GaAs vertical-cavity surface-emitting lasers. <i>Optical and Quantum Electronics</i> , <b>2004</b> , 36, 331-347	2.4	17
107	CCD thermoreflectance spectroscopy as a tool for thermal characterization of quantum cascade lasers. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 115006	1.8	16
106	Growth and characterization of high quality LPEE GaAs bulk crystals. <i>Journal of Crystal Growth</i> , <b>1987</b> , 85, 136-141	1.6	13
105	Direct Au/Au bonding technology for high performance GaAs/AlGaAs quantum cascade lasers. <i>Optical and Quantum Electronics</i> , <b>2015</b> , 47, 893-899	2.4	11
104	Thermal processes in high-power laser bars investigated by spatially resolved thermoreflectance. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2008</b> , 19, 150-154	2.1	11
103	Mid-Infrared GaAs/AlGaAs Quantum Cascade Lasers Technology. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, S-45-S-47	3.47	11
102	Impact of Injector Doping on Threshold Current of Mid-Infrared Quantum Cascade Laser: Non-Equilibrium Green's Function Analysis. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2015</b> , 21, 124-133	3.8	10
101	Low-resistance p-type ohmic contacts for high-power InGaAs/GaAs-980 nm CW semiconductor lasers. <i>Vacuum</i> , <b>2008</b> , 82, 977-981	3.7	10
100	Photoluminescence mapping and angle-resolved photoluminescence of MBE-grown InGaAs/GaAs RC LED and VCSEL structures. <i>Thin Solid Films</i> , <b>2002</b> , 412, 114-121	2.2	9
99	Dual Contribution to the Stokes Shift in InGaN/GaN Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 228, 111-114	1.3	9
98	Many-body effects in highly p-type modulation-doped GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As quantum wells. <i>Physical Review B</i> , <b>2000</b> , 61, 2794-2798	3.3	9
97	Characterization of the superlattice region of a quantum cascade laser by secondary ion mass spectrometry. <i>Nanoscale</i> , <b>2017</b> , 9, 17571-17575	7.7	8
96	Investigation of thermal management in optically pumped, antimonide VECSELs. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 558-561	1.8	8
95	Crystal growth of GaP doped with nitrogen under high nitrogen pressure. <i>Journal of Crystal Growth</i> , <b>1985</b> , 72, 711-716	1.6	8
94	High numerical aperture large-core photonic crystal fiber for a broadband infrared transmission. <i>Infrared Physics and Technology</i> , <b>2016</b> , 79, 10-16	2.7	7

93	Time resolved FTIR study of spectral tuning and thermal dynamics of mid-IR QCLs <b>2014</b> ,		7
92	Room temperature, single mode emission from two-section coupled cavity InGaAs/AlGaAs/GaAs quantum cascade laser. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 133103	2.5	7
91	Influence of Operating Conditions on Quantum Cascade Laser Temperature. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 630-634	1.9	7
90	MBE growth of planar microcavities with distributed Bragg reflectors. <i>Thin Solid Films</i> , <b>2000</b> , 367, 290-294	4.2	7
89	Above room temperature operation of InGaAs/AlGaAs/GaAs quantum cascade lasers. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 035006	1.8	6
88	Multi-step interrupted-growth MBE technology for GaAs/AlGaAs (~9.4 $\mu\text{m}$ ) room temperature operating quantum-cascade lasers. <i>Opto-electronics Review</i> , <b>2012</b> , 20,	2.4	6
87	Heat Dissipation Schemes in AlInAs/InGaAs/InP Quantum Cascade Lasers Monitored by CCD Thermoreflectance. <i>Photonics</i> , <b>2017</b> , 4, 47	2.2	6
86	Formation of coupled-cavities in quantum cascade lasers using focused ion beam milling. <i>Microelectronics Reliability</i> , <b>2015</b> , 55, 2142-2146	1.2	6
85	Low-temperature grown near surface semiconductor saturable absorber mirror: Design, growth conditions, characterization, and mode-locked operation. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 053101	2.5	6
84	Thermal properties of high power laser bars investigated by spatially resolved thermoreflectance spectroscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2007</b> , 204, 422-429	1.6	6
83	Transport and tunneling within a compressible electron liquid in wires and rings of GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As heterostructures. <i>Physical Review B</i> , <b>1998</b> , 58, 16252-16261	3.3	6
82	High-resolution mirror temperature mapping in GaN-based diode lasers by thermoreflectance spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 020302	1.4	5
81	Numerical simulation of GaAs-based mid-infrared one-phonon resonance quantum cascade laser. <i>Optical and Quantum Electronics</i> , <b>2017</b> , 49, 1	2.4	5
80	On the onset of strain relaxation in the Al <sub>0.45</sub> Ga <sub>0.55</sub> As/In <sub>x</sub> Ga <sub>1-x</sub> As active region in quantum cascade laser structures. <i>Journal of Applied Crystallography</i> , <b>2017</b> , 50, 1376-1381	3.8	5
79	Optimization of MBE Growth Conditions of InAlAs Waveguide Layers for InGaAs/InAlAs/InP Quantum Cascade Lasers. <i>Materials</i> , <b>2019</b> , 12,	3.5	5
78	Temperature induced degradation mechanisms of AlInAs/InGaAs/InP quantum cascade lasers. <i>Materials Research Express</i> , <b>2018</b> , 5, 016204	1.7	5
77	Optical Properties of Active Regions in Terahertz Quantum Cascade Lasers. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , <b>2016</b> , 37, 710-719	2.2	5
76	High-resolution X-ray characterization of mid-IR Al <sub>0.45</sub> Ga <sub>0.55</sub> As/GaAs Quantum Cascade Laser structures. <i>Thin Solid Films</i> , <b>2014</b> , 564, 339-344	2.2	5

75	Advanced optical characterization of AlGaAs/GaAs superlattices for active regions in quantum cascade lasers. <i>Optical and Quantum Electronics</i> , <b>2015</b> , 47, 945-952	2.4	5
74	Electrical and optical characterisation of mid-IR GaAs/AlGaAs quantum cascade lasers <b>2012</b> ,		5
73	Photoreflectance Study of GaN/AlGaN Structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 491-494		5
72	Thermal properties of high-power diode lasers investigated by microthermography <b>2005</b> ,		5
71	Formation of Dislocations in InGaAs/GaAs Heterostructures. <i>Physica Status Solidi A</i> , <b>1999</b> , 171, 275-282		5
70	Stoichiometry changes in III $\nu$ compounds under ion bombardment. <i>Nuclear Instruments &amp; Methods in Physics Research</i> , <b>1983</b> , 209-210, 621-627		5
69	Molecular Beam Epitaxy Growth for Quantum Cascade Lasers. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, 806-813	3.6	5
68	Multimode instabilities in mid-infrared quantum cascade lasers. <i>Photonics Letters of Poland</i> , <b>2013</b> , 5,	2.1	5
67	Examination of thermal properties and degradation of InGaN - based diode lasers by thermoreflectance spectroscopy and focused ion beam etching. <i>AIP Advances</i> , <b>2017</b> , 7, 075107	1.5	4
66	High performance GaAs/AlGaAs quantum cascade lasers: optimization of electrical and thermal properties <b>2012</b> ,		4
65	Experimental analysis of thermal properties of AlGaAs/GaAs quantum cascade lasers <b>2012</b> ,		4
64	Conductance noise of submicron wires in the regime of quantum Hall effect. <i>Physica B: Condensed Matter</i> , <b>1998</b> , 256-258, 69-73	2.8	4
63	Characterization of (Al)GaAs/AlAs distributed Bragg mirrors grown by MBE and LP MOVPE techniques. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4094-4101	1.6	4
62	Investigation of oval defects in (In)Ga(Al)As/GaAs heterostructures by spatially resolved photoluminescence and micro-cathodoluminescence. <i>Materials Science in Semiconductor Processing</i> , <b>2006</b> , 9, 25-30	4.3	4
61	Investigations of optical properties of active regions in vertical cavity surface emitting lasers grown by MBE. <i>Thin Solid Films</i> , <b>2002</b> , 412, 107-113	2.2	4
60	Threshold simulation of 1.3- $\mu$ m oxide-confined in-plane quantum-dot (InGa)As/GaAs lasers. <i>Optical and Quantum Electronics</i> , <b>2003</b> , 35, 675-692	2.4	4
59	Output power saturation in InAs/GaAs quantum dot lasers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 1351-1354		4
58	Room temperature AlInAs/InGaAs/inP quantum cascade lasers. <i>Photonics Letters of Poland</i> , <b>2014</b> , 6,	2.1	4

57	Comparison of quantum cascade structures for detection of nitric oxide at ~ 5.2 $\mu\text{m}$ . <i>Optical and Quantum Electronics</i> , <b>2019</b> , 51, 1	2.4	3
56	Optimization of Cavity Designs of Tapered AlInAs/InGaAs/InP Quantum Cascade Lasers Emitting at 4.5 $\mu\text{m}$ . <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2019</b> , 25, 1-9	3.8	3
55	Quantification of thermoreflectance temperature measurements in high-power semiconductor devices lasers and laser bars. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 1373-1378	1.8	3
54	Thermal effects in 2.x $\mu\text{m}$ vertical-external-cavity-surface-emitting lasers. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 053107	2.5	3
53	GaAs/AlGaAs (~9.4 $\mu\text{m}$ ) quantum cascade lasers operating at 260 K. <i>Bulletin of the Polish Academy of Sciences: Technical Sciences</i> , <b>2010</b> , 58,		3
52	Tailoring of optical mode profiles of high-power diode lasers evidenced by near-field photocurrent spectroscopy. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 101103	3.4	3
51	Passivation of InP(100) substrates: first stages of nitridation by thin InN surface overlayers studied by electron spectroscopies. <i>Surface and Interface Analysis</i> , <b>2005</b> , 37, 615-620	1.5	3
50	Resonant Cavity Enhanced Photonic Devices. <i>Acta Physica Polonica A</i> , <b>2002</b> , 101, 105-118	0.6	3
49	Coupled-cavity AlInAs/InGaAs/InP quantum cascade lasers fabricated by focused ion beam processing. <i>JPhys Photonics</i> , <b>2019</b> , 1, 015001	2.5	2
48	A novel method to calculate a near field of widely divergent laser beams. <i>Optical and Quantum Electronics</i> , <b>2016</b> , 48, 1	2.4	2
47	The determination of the chemical composition profile of the GaAs/AlGaAs heterostructures designed for quantum cascade lasers by means of synchrotron radiation. <i>Radiation Physics and Chemistry</i> , <b>2011</b> , 80, 1112-1118	2.5	2
46	Interisland exciton migration and enhanced bound exciton recombination in an AlGaAs/GaAs quantum well structure grown by molecular beam epitaxy without growth interruptions at interfaces. <i>Semiconductor Science and Technology</i> , <b>1997</b> , 12, 1416-1421	1.8	2
45	Optical Properties of p-Type Modulation Doped GaAs/AlGaAs Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>1998</b> , 210, 615-620	1.3	2
44	Facet Heating Mechanisms in High Power Semiconductor Lasers Investigated by Spatially Resolved Thermoreflectance <b>2007</b> ,		2
43	Thermoreflectance Measurements of the Temperature Distributions in Laser Diodes with Non Injected Facet. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 916, 1		2
42	Long-wavelength strained-layer InGaAs/GaAs quantum-well lasers grown by molecular beam epitaxy. <i>Microwave and Optical Technology Letters</i> , <b>2001</b> , 29, 75-77	1.2	2
41	Magneto-optical studies of highly p-type modulation-doped GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As quantum wells. <i>Physical Review B</i> , <b>2000</b> , 62, 15952-15961	3.3	2
40	Exciton dynamics in thin quantum wells grown by MBE. <i>Thin Solid Films</i> , <b>1995</b> , 267, 84-88	2.2	2

39	Visible Light Emission from Porous Silicon. <i>Acta Physica Polonica A</i> , <b>1992</b> , 82, 914-918	0.6	2
38	Identification of Residual Impurities in Si-Doped MBE Grown GaAs. <i>Acta Physica Polonica A</i> , <b>1995</b> , 88, 775-778	0.6	2
37	Development of ( $\lambda$ 9.4 $\mu$ m) GaAs-Based Quantum Cascade Lasers Operating at the Room Temperature. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , <b>2011</b> , 91-100	0.2	2
36	Coupled Cavity Mid-IR Quantum Cascade Lasers Fabricated by Dry Etching. <i>Photonics</i> , <b>2020</b> , 7, 45	2.2	2
35	Tuning quantum cascade laser wavelength by the injector doping. <i>Applied Physics B: Lasers and Optics</i> , <b>2018</b> , 124, 1	1.9	2
34	Field distribution in waveguide of mid-infrared strain-compensated InAlAs/InGaAs/InP quantum cascade laser. <i>Optical and Quantum Electronics</i> , <b>2017</b> , 49, 1	2.4	1
33	Degradation of AlInAs/InGaAs/InP quantum cascade lasers due to electrode adhesion failure. <i>Microelectronics Reliability</i> , <b>2019</b> , 99, 113-118	1.2	1
32	Single-mode enhancement in coupled-cavity quantum cascade lasers <b>2016</b> ,		1
31	Mid-IR quantum cascade lasers: Device technology and non-equilibrium Green's function modeling of electro-optical characteristics (Phys. Status Solidi B 6/2014). <i>Physica Status Solidi (B): Basic Research</i> , <b>2014</b> , 251,	1.3	1
30	AlGaAs/GaAs quantum cascade lasers for gas detection systems <b>2011</b> ,		1
29	Determination of energy difference and width of minibands in GaAs/AlGaAs superlattices by using Fourier transform photoreflectance and photoluminescence. <i>Opto-electronics Review</i> , <b>2011</b> , 19,	2.4	1
28	Development of ( $\lambda$ 9.4 $\mu$ m) GaAs-based quantum cascade lasers <b>2009</b> ,		1
27	Photoluminescence studies of optical properties of VECSEL active region under high excitation conditions. <i>Journal of Physics: Conference Series</i> , <b>2009</b> , 146, 012031	0.3	1
26	Passively modelocked bi-directional vertical external ring cavity surface emitting laser <b>2008</b> ,		1
25	Improvement of quantum efficiency of MBE grown AlGaAs/InGaAs/GaAs edge emitting lasers by optimisation of construction and technology. <i>Vacuum</i> , <b>2007</b> , 82, 383-388	3.7	1
24	Investigation of thermal processes in high power laser bars by thermoreflectance spectroscopy <b>2007</b> ,		1
23	Electron microscopy study of advanced heterostructures for optoelectronics. <i>Materials Chemistry and Physics</i> , <b>2003</b> , 81, 244-248	4.4	1
22	Whole wafer assessment of electronic materials by scanning photoluminescence and surface photovoltage. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1993</b> , 20, 186-189	3.1	1

21	Response to Comment on Native acceptor levels in Ga-rich GaAs [J. Appl. Phys. 65, 596 (1989)]. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 7619-7619	2.5	1
20	Growth and luminescence properties of GaSb single crystals. <i>Acta Physica Hungarica</i> , <b>1985</b> , 57, 303-308		1
19	Pulsed laser annealing of nitrogen-implanted GaP. <i>Materials Letters</i> , <b>1985</b> , 3, 141-144	3.3	1
18	Electronic States in Type-II Superlattices. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, S-65-S-68	0.6	1
17	Optoelectronic properties of InAs/GaSb superlattices with asymmetric interfaces. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 367, 012014	0.3	0
16	Optical examination of high contrast grating fabricated by focused-ion beam etching. <i>Optical and Quantum Electronics</i> , <b>2016</b> , 48, 1	2.4	
15	Room temperature photoluminescence studies of nitrided InP(100) surfaces. <i>Materials Science and Engineering C</i> , <b>2006</b> , 26, 378-382	8.3	
14	Analysis of Threshold Current and Wall-Plug Efficiency of Diode Lasers with Asymmetric Facet Reflectivity. <i>Optical and Quantum Electronics</i> , <b>2004</b> , 36, 443-457	2.4	
13	Investigation of Indium Tin Oxide (ITO) films for the VCSEL laser with dielectric Bragg reflectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 396-400		
12	The influence of erbium on the physical properties of GaN crystals grown from N solution in Ga at high nitrogen pressure. <i>High Pressure Research</i> , <b>2000</b> , 18, 35-39	1.6	
11	Transmission electron microscopy study of the formation of a contamination layer on the surface of porous silicon. <i>Journal of Materials Science: Materials in Electronics</i> , <b>1994</b> , 5, 280-283	2.1	
10	A novel technique for investigation of luminescence properties of Ga <sub>1-x</sub> In <sub>x</sub> P LPE layers with a small In content. <i>Journal Physics D: Applied Physics</i> , <b>1981</b> , 14, 127-134	3	
9	The kinetics of Si incorporation in Ga melt for LPE growth of GaP doped with nitrogen from NH <sub>3</sub> . <i>Journal of Crystal Growth</i> , <b>1982</b> , 60, 434-440	1.6	
8	Physical Principles of the Operation of Semiconductor Lasers <b>1991</b> , 11-69		
7	The Design and Basic Characteristics of Semiconductor Lasers <b>1991</b> , 107-198		
6	Low Threshold Room Temperature AlGaAs/GaAs GRIN SCH SQW Lasers Grown by MBE. <i>Acta Physica Polonica A</i> , <b>1996</b> , 90, 847-850	0.6	
5	Fermi-Edge Singularity in Excitonic Spectra of Modulation Doped AlGaAs/GaAs Quantum Wells. <i>Acta Physica Polonica A</i> , <b>1996</b> , 90, 751-754	0.6	
4	Inter-Island Energy Transfer in AlGaAs/GaAs Quantum Wells Grown by Molecular Beam Epitaxy. <i>Acta Physica Polonica A</i> , <b>1996</b> , 90, 1007-1011	0.6	



- 3 Theoretical Analysis of Optical Gain in Quantum Well Lasers Including Valence-Band Mixing Effect. *Acta Physica Polonica A*, **1997**, 92, 903-907 0.6
- 2 Fermi-Edge Singularity in Luminescence Spectra of P-Type Modulation Doped AlGaAs/GaAs Quantum Wells. *Acta Physica Polonica A*, **1998**, 94, 265-270 0.6
- 1 Angular and Temperature Tuning of Emission from Vertical-External-Cavity Surface-Emitting Lasers (VECSELs). *Acta Physica Polonica A*, **2008**, 114, 1437-1443 0.6